



INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

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Attorney Docket Number

41994/JWP/C766

Application Number

09/895,791

Filing Date

June 29, 2001

Applicant(s)

Richard C. Flagan, et al.

Group Art Unit

1762

Examiner Name

to be assigned

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| EXAMINER INITIALS | Cite No. <sup>1</sup> | DOCUMENT NUMBER<br>Number - kind code <sup>2</sup> .<br>(If known) | PUBLICATION DATE<br>MM-DD-YYYY | NAME OF PATENTEE |
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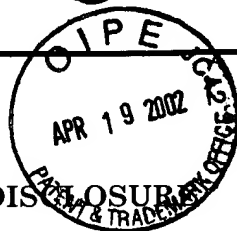
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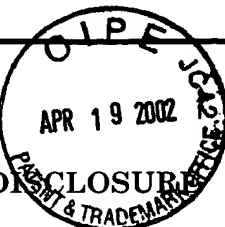
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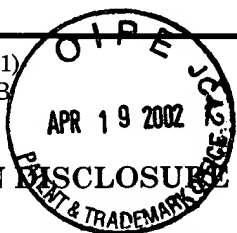
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